

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK2162

AUDIO FREQUENCY POWER AMPLIFIER APPLICATION

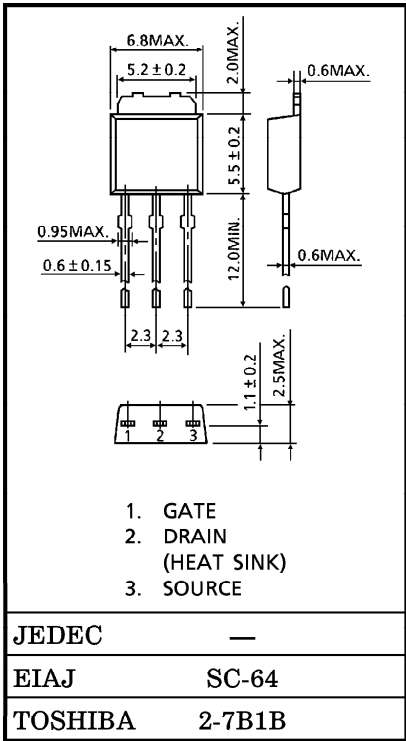
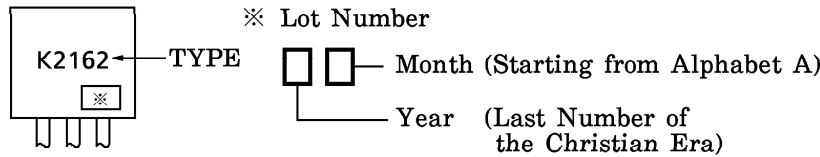
INDUSTRIAL APPLICATIONS  
Unit in mm

- High Breakdown Voltage :  $V_{DSS}=180V$
- High Forward Transfer Admittance :  $|Y_{fs}|=0.7S$  (Typ.)
- Complementary to 2SJ338

MAXIMUM RATINGS ( $T_a=25^{\circ}C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DSS}$	180	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current	$I_D$	1	A
Power Dissipation ( $T_c=25^{\circ}C$ )	$P_D$	20	W
Channel Temperature	$T_{ch}$	150	$^{\circ}C$
Storage Temperature Range	$T_{stg}$	$-55\sim 150$	$^{\circ}C$

MARKING



Weight : 0.36g

ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0, V_{GS}=\pm 20V$	—	—	$\pm 100$	$\mu A$
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=10mA, V_{GS}=0V$	180	—	—	V
Gate-Source Cut-off Current	$V_{GS(OFF)}$	$V_{DS}=10V, I_D=10mA$	1.4	—	2.8	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	$I_D=0.6A, V_{GS}=10V$	—	1.7	3.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=0.3A$	—	0.7	—	S
Input Capacitance	$C_{iss}$	$V_{DS}=10V, V_{GS}=10, f=1MHz$	—	170	—	pF
Output Capacitance	$C_{oss}$		—	45	—	pF
Reverse Transfer Capacitance	$C_{rss}$		—	17	—	pF

This transistor is the electrostatic sensitive device.  
Plese handle with caution.

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